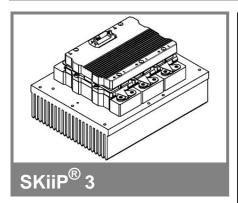
SKiiP 1513GB172-3DL



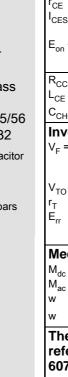
2-pack-integrated intelligent Power System

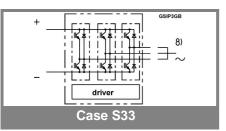
Power section SKiiP 1513GB172-3DL

Data

Power section features

- SKiiP technology inside
- Trench IGBTs
- CAL diode technology
- · Integrated current sensor
- · Integrated teperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP[®] 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized file no. E63532
- with assembly of suitable MKP capacitor per terminal
- AC connection busbars must be connected by the user; copper busbars available on request



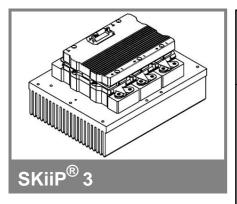


Absolute	Maximum Ratings T _s	= 25 °C, unless otherwise specified				
Symbol	Conditions	Values	Units			
IGBT						
V _{CES} V _{CC} 1)	Operating DC link voltage	1700 1200	V V			
V _{GES}	T _s = 25 (70) °C	± 20 1500 (1125)	V A			
Inverse diode						
I _F = - I _C I _{FSM} I ² t (Diode)	$T_s = 25 (70) ^{\circ}C$ $T_j = 150 ^{\circ}C, t_p = 10 \text{ ms; sin}$ Diode, $T_i = 150 ^{\circ}C, 10 \text{ ms}$	1250 (950) 10200 520	A A kA²s			
T _j , (T _{stg})	rms, AC, 1 min, main terminals to heat sink	- 40 + 150 (125) 4000	°C V			
I _{AC-terminal}	per AC terminal, rms, $T_s = 70 ^{\circ}\text{C}$, $T_{\text{terminal}} < 115 ^{\circ}\text{C}$	400	Α			

Characte	Characteristics T				T _s = 25 °C, unless otherwise specified			
Symbol Conditions			min.	typ.	max.	Units		
IGBT	•				•			
V _{CEsat}	I _C = 900 A measured at	A, T _j = 25 (1 terminal	25) °C;			1,9 (2,2)	2,4	V
V _{CEO}		25) °C; at to 25) °C; at to				1 (0,9) 1 (1,4)	1,2 (1,1) 1,3 (1,7)	V mΩ
I _{CES}	$V'_{GE} = 0 V$ $T_i = 25 (12)$, V _{CE} = V _C 25) °C	ES'			3,6 (216)		mA
E _{on} + E _{off}	$I_{\rm C}^{\prime} = 900 A$, V _{CC} = 90	0 V			585		mJ
	T _j = 125 °	C, V _{CC} = 1	200 V			863		mJ
R _{CC+EE}	terminal c	hip, T _i = 25	5 °C			0,17		mΩ
L _{CE}	top, bottor	m ´				4		nΗ
C _{CHC}	per phase	, AC-side				5,1		nF
Inverse o	diode							
$V_F = V_{EC}$	I _F = 900 A measured at	, T _j = 25 (1 terminal	25) °C			2 (1,8)	2,15	V
V_{TO}	$T_i = 25 (12)$	25) °C				1,1 (0,8)	1,2 (0,9)	V
r _T	$T_i = 25 (12)$	25) °C				1 (1,1)	1,1 (1,2)	mΩ
E _{rr}	$I_{\rm C} = 900 A$	$V_{CC} = 90$	0 V			108		mJ
	T _j = 125 °	C, V _{CC} = 1	200 V			128		mJ
Mechani	cal data							
M_{dc}		ıals, SI Uni			6		8	Nm
M _{ac}		als, SI Uni			13		15	Nm
W		System w/c	heat sink			2,4		kg
W	heat sink					7,5		kg
Thermal characteristics (PX 16 heat sink with fan SKF16B-230-1); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc.IEC 60747-15)								
$R_{th(j-s)l}$	per IGBT						0,02	K/W
R _{th(j-s)D}	per diode						0,038	K/W
Z _{th}	R _i (mK/W) (max. values)				tau _i (s)			
	1	2	3	4	1	2	3	4
$Z_{th(j-r)l}$	3,4	9,6	7	0	363	0,18	0,04	1
$Z_{th(j-r)D}$	12	12	18	20	30	5	0,25	0,04
$Z_{th(r-a)}$	2,1	20	5,5	1,4	210	85	11	0,4

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SKiiP 1513GB172-3DL



2-pack-integrated intelligent Power System

2-pack integrated gate driver SKiiP 1513GB172-3DL

Data

Gate driver features

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and

DC-bus voltage (option)

- Short circuit protection
- · Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

Absolute Maximum Ratings		T _a = 25 °C, unless otherwise specified			
Symbol	Conditions	Values	Units		
V_{S2}	unstabilized 24 V power supply	30	V		
V_{i}	input signal voltage (high)	15 + 0,3	V		
dv/dt	secondary to primary side	75	kV/μs		
V_{isollO}	input / output (AC, rms, 2 s)	4000	V		
V _{isoIPD}	partial discharge extinction voltage, rms, $Q_{PD} \le 10 \text{ pC}$;	1500	V		
V _{isol12}	output 1 / output 2 (AC, rms, 2 s)	1500	V		
f _{sw}	switching frequency	9	kHz		
f _{out}	output frequency for I _{peak(1)} =I _C	9	kHz		
$T_{op} (T_{stg})$	operating / storage temperature	- 40 + 85	°C		

Characte	eristics	(T _a = 25 °C)			= 25 °C)
Symbol	Conditions	min.	typ.	max.	Units
V_{S2}	supply voltage non stabilized	13	24	30	V
I _{S2}	V _{S2} = 24 V	380+34*f/kHz+0,00015*(I _{AC} /A) ²			mA
V _{iT+}	input threshold voltage (High)			12,3	V
V_{iT-}	input threshold voltage (Low)	4,6			V
R _{IN}	input resistance		10		kΩ
C _{IN}	input capacitance		1		nF
t _{d(on)IO}	input-output turn-on propagation time		1,3		μs
t _{d(off)IO}	input-output turn-off propagation time		1,3		μs
tpERRRESET	error memory reset time		9		μs
t_{TD}	top / bottom switch interlock time		3,3		μs
I _{analogOUT}	max. 5 mA; 8 V corresponds to 15 V supply voltage for external components		1500		Α
I _{s1out}	max. load current			50	mA
I _{TRIPSC}	over current trip level (I _{analog} OUT = 10 V)	110	1875	120	A
T_tp U_DCTRIP	over temperature protection U _{DC} -protection (U _{analog OUT} = 9 V);	110	not implemented	120 d	°C V
	(option for GB types)		,	-	

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